V_L-wa alaya Institution of Engineering and Technology BE I Year EXAMINATION Feb-March 2022 CS(A), CS(B), and all EX ETRIC4: BASIC ELECTRONICS

Note: Attempt any two part from each question

Max. Marks: 60

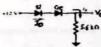
Q.1 (a) Write down difference between following.

n-type and p-type semiconductor materials. donor and acceptor impurities. majority and minority carriers.

11.

(b) Determine Vo and In for the given circuit.

(6)



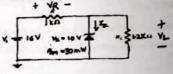
Draw the V-I characteristics of Silicon diode, Zener diode, LED, Photo diode and ideal diode. (c)

(6)

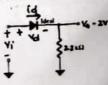
Q.2 (a) Determine Vo for the given network.

(b) Determine VL, VR, Iz, and Pz for given circuit.

(6)



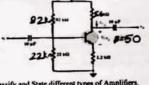
Assuming an ideal diode, sketch vi, vd, and id for the half-wave rectifier of Fig. The input is a sinusoidal waveform with a frequency of 60 Hz. Repeat, Problem with a silicon diode (VT =0.7 V). (6) (c)



Sketch Output characteristic of BJT in Com What kind of information does it reveals? Derive expressions for Stability Factors S, 5 Q.3 (a)

ers S, S' and S" for BJT in Collector to Base I

(b) 1 Determine Q- point for th (6)



Classify and State different types of Amplifiers.

Explain working of BJT Differential Amplifier circuit.

(6) (6)

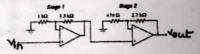
(6)

(6)

Explain with necessary circuits how OP-AMP can be used to filter different frequency signals Q.4 (a)

It is require to implement the function C=4 $^{\circ}$ (A-B) in hardware, where A and B are two voltage sources and C is the output voltage. Draw and (6) explain the circuit to meet the same.

Calculate the voltage gain for each stage of this amplifier circuit, then calculate the overall voltage gain: (6)



Q.5 (a) Sketch and explain re model for BJT in CE configuration. State relation between a, B and y.

(b) Compare positive and negative feedback with the help of block diagram.

State the purpose of using Schmitt Trigger. Draw the circuit and Explain (6) the same.

BE I year Computer Engineering B Subject Name: Basic Electronics Subject Code: - 1ETRC4

Time: 3 hours

Max Marks:60

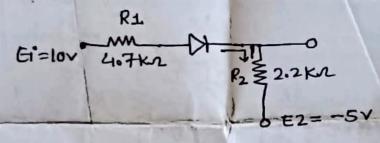
(6)

Note:- All question carry equal marks. Attempt any two part from each question

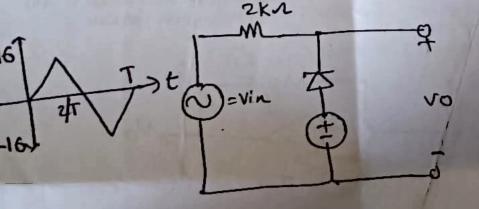
- Q.1 a) Draw the ideal diode V-I characteristic and explain the working of the PN junction (6)
 - b) Consider a pn junction at equilibrium at room temperature (T=300K) for which the doping concentrations are Na = 10¹²/cm³ and Nd = 10¹¹/cm³ and the cross-sectional area A=10⁻²cm². Calculate pn the name of Name and Oi Use pig 1.2×10⁹/cm³
 - area A=10⁻²cm². Calculate p_p, n_{po}, n_n, p_{po}, V₀, W, xn, xp and Qj. Use ni=1.2x10⁹/cm³.

 Calculate p_p, n_{po}, n_n, p_{po}, V₀, W, xn, xp and Qj. Use ni=1.2x10⁹/cm³.

 Calculate p_p, n_{po}, n_n, p_{po}, V₀, W, xn, xp and Qj. Use ni=1.2x10⁹/cm³.
- Q.2 a) Determine ID, IRI, IR2, V0, VRI and VR2 use practical diode model.



b) Determine the output vo waveform for circuit below.



c) Explain the working of a full wave bridge rectifier with the help of a circuit diagram. Also, draw output waveform

